Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S32	79	(semiconductor adj substrate) with stack with interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 11:38
S33	272635	spiral	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 11:33
S34	1	S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 11:35
S35	11204	(p adj well) and (n adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 12:43
S36	2	S32 and S35	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 11:37
S37	296	(semiconductor adj substrate) SAME stack SAME interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 11:38
S38	7	S35 and S37	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 11:40
S39	286	inductor WITH (semiconductor adj substrate) SAME spiral	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 12:04
S40	11	S35 and S39	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 11:41
S41	4	("20010048135" | "20030151115" | "6426543" | "6452249").PN. OR ("6867475").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/02 11:58
S42	2	("20020123159").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/01/02 11:58

S43	421	induct$3r WITH (semiconductor adj substrate) SAME (spiral conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 13:49
S44	15	S35 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 12:05
S46	57	S43 and damascene	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 13:26
S47	2	("20020158306").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/01/02 13:26
S48	17	S43 and ((shallow adj trench) sti)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/02 14:37